

# NOT RECOMMENDED FOR NEW DESIGN USE DMN3030LSS



**DMN3031LSS** 

#### SINGLE N-CHANNEL ENHANCEMENT MODE MOSFET

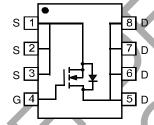
#### **Features**

- Low On-Resistance
  - $18.5 \text{m}\Omega$  @  $V_{GS} = 10 \text{V}$
  - 31mΩ @ V<sub>GS</sub> = 4.5V
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 2)
- "Green" Device (Note 4)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.072g (approximate)

SOP-8L



TOP VIEW Internal Schematic



TOP VIEW

### **Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

	Characteristic			Symbol	Value	Units
Drain-Source Voltage				V <sub>DSS</sub>	30	V
Gate-Source Voltage				$V_{GSS}$	±20	V
Drain Current (Note 1)	Steady State	$T_A = 25$ °C $T_A = 70$ °C		I <sub>D</sub>	9 6.75	Α
Pulsed Drain Current (Note 3	3)		4	I <sub>DM</sub>	40	Α

### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 1)	$P_{D}$	2.5	W
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	50	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes:

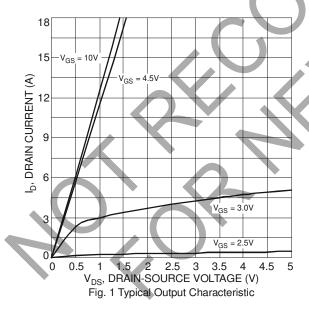
- Device mounted on 2 oz copper pad layout with R<sub>0JA</sub> = 50°C/W.
- 2. No purposefully added lead.
- 3. Pulse width ≤10µS, Duty Cycle ≤1%.
- 4. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.

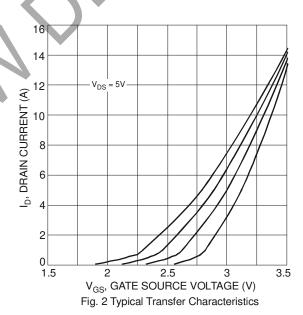


## **Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

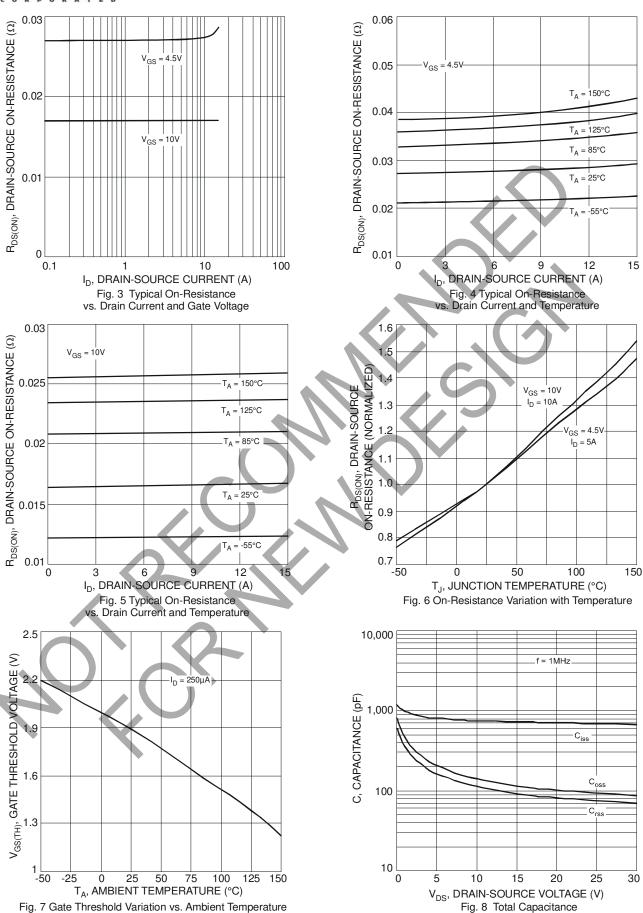
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)						
Drain-Source Breakdown Voltage	$BV_{DSS}$	30			V	$V_{GS} = 0V, I_D = 250 \mu A$
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 30V, V_{GS} = 0V$
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 5)						
Gate Threshold Voltage	$V_{GS(th)}$	1	_	2.1	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$
Static Drain-Source On-Resistance	D		15	18.5	mΩ	$V_{GS} = 10V, I_D = 9A$
Static Dialii-Source Off-Resistance	R <sub>DS (ON)</sub>		26	31		$V_{GS} = 4.5V$ , $I_D = 7A$
Forward Transconductance	g <sub>fs</sub>	_	5.8		S	$V_{DS} = 10V, I_D = 9A$
Diode Forward Voltage (Note 5)	$V_{SD}$	0.5	0.7	1.2	V	$V_{GS} = 0V, I_S = 2.1A$
DYNAMIC CHARACTERISTICS						
Input Capacitance	$C_{iss}$	_	741	_	pF	V 45V V 0V
Output Capacitance	$C_{oss}$	_	124	_	pF	$V_{DS} = 15V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	$C_{rss}$	_	95	_	pF	1 - 1.0W112
Gate Resistance	R <sub>G</sub>	0.30	0.88	1.5	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1.0MHz$
SWITCHING CHARACTERISTICS						
Total Cata Chausa	0	_	7.6	12		$V_{DS} = 15V$ , $V_{GS} = 4.5V$ , $I_{D} = 9A$
Total Gate Charge	Qg	_	16.7	25	nC	
Gate-Source Charge	$Q_{gs}$	_	1.9		IIC	$V_{DS} = 15V$ , $V_{GS} = 10V$ , $I_{D} = 9A$
Gate-Drain Charge	$Q_{gd}$	_	5.2			` /
Turn-On Delay Time	t <sub>d(on)</sub>	_	4.0	<i>//</i>		
Rise Time	t <sub>r</sub>	-	4.4	_	-	$V_{GS} = 10V, V_{DS} = 15V,$
Turn-Off Delay Time	t <sub>d(off)</sub>	4	23.0		ns	$R_L = 15\Omega$ , $R_G = 6\Omega$
Fall Time	t <sub>f</sub>	11	9.4			

Notes: 5. Short duration pulse test used to minimize self-heating effect

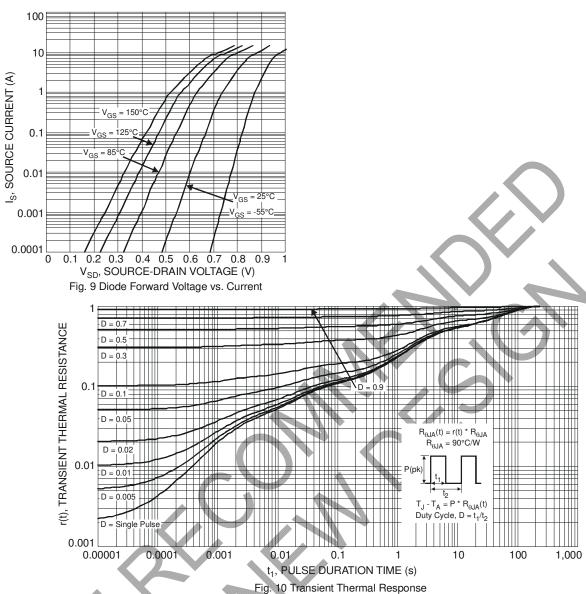










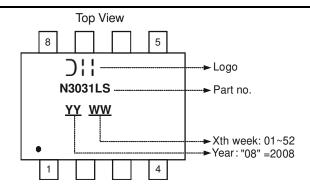


### Ordering Information (Note 6)

Part Number	Case	Packaging
DMN3031LSS-13	SO-8	2500/Tape & Reel

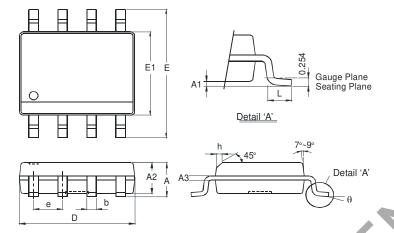
Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

## **Marking Information**



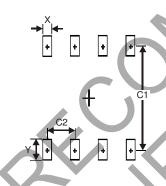


## **Package Outline Dimensions**



SO-8					
Dim	Min	Max			
Α	-	1.75			
<b>A</b> 1	0.10	0.20			
A2	1.30	1.50			
A3	0.15	0.25			
b	0.3	0.5			
D	4.85	4.95			
Е	5.90	6.10			
E1	3.85	3.95			
е	1.27 Typ				
h		0.35			
J	0.62	0.82			
θ	0°	8°			
All Dimensions in mm					

## **Suggested Pad Layout**



Dimensions	Value (in mm)
Х	0.60
Υ	1.55
C1	5.4
C2	1.27



**DMN3031LSS** 



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